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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/695,307	10/28/2003	Seetharaman Sridhar	TI-36658 (032350.B546)	4176
23494	7590	01/04/2007	EXAMINER	
TEXAS INSTRUMENTS INCORPORATED P O BOX 655474, M/S 3999 DALLAS, TX 75265			WILCZEWSKI, MARY A	
			ART UNIT	PAPER NUMBER
			2822	
SHORTENED STATUTORY PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE		
3 MONTHS	01/04/2007	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

<b>Office Action Summary</b>	Application No.	Applicant(s)
	10/695,307	SRIDHAR ET AL.
	Examiner M. Wilczewski	Art Unit 2822

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --  
**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

1) Responsive to communication(s) filed on 04 October 2006.  
 2a) This action is FINAL.                    2b) This action is non-final.  
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

4) Claim(s) 1-5 and 8-20 is/are pending in the application.  
 4a) Of the above claim(s) 17-20 is/are withdrawn from consideration.  
 5) Claim(s) \_\_\_\_\_ is/are allowed.  
 6) Claim(s) 1-5 and 8-16 is/are rejected.  
 7) Claim(s) \_\_\_\_\_ is/are objected to.  
 8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

9) The specification is objected to by the Examiner.  
 10) The drawing(s) filed on October 28, 2003 is/are: a) accepted or b) objected to by the Examiner.  
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

#### Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
 a) All    b) Some \* c) None of:  
 1. Certified copies of the priority documents have been received.  
 2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

#### Attachment(s)

1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____
3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date _____	5) <input type="checkbox"/> Notice of Informal Patent Application
	6) <input type="checkbox"/> Other: _____

## DETAILED ACTION

This Office action is in response to Amendment filed on October 4, 2006.

### ***Response to Arguments***

Applicant's arguments with respect to claims 1-5 and 8-16 have been considered but are moot in view of the new ground(s) of rejection.

### ***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-5 and 8-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Xiang et al., US Patent 7,071,065, in view of Cabral, Jr. et al., US Patent 6,690,072, both newly cited.

Xiang et al. disclose a method for forming MOSFETs which comprises a semiconductor substrate 40 having a source region, a channel region, and a drain region, wherein the channel region resides between the source and drain regions and a gate region 54 resides over the channel region 64, see figures 3b-3c; forming a silicon-germanium layer within the substrate in each of the source and drain regions in the substrate and below a plane defined by an uppermost surface of the substrate, see figures 3d and 3e; and forming a silicide layer 74 in each of the source and drain

regions, see figure 3i. Xiang et al. lack anticipation only of forming a silicon layer outwardly from the substrate and the silicon-germanium layer in each of the source and drain regions.

Cabral, Jr. et al. teach to form a silicon layer outwardly from the substrate and the silicon-germanium layer in each of the source and drain regions. By using the sacrificial silicon overlayer within which to form the silicide the method of Cabral, Jr. et al. overcomes the problem of reaction of the metal with the SiGe layer in the source/drain regions which forms undesirable multiphase microstructures, see figures 1A-1E; column 1, lines 60-63; column 4, lines 41-48 and lines 59-61; and column 5, line 65 bridging column 6 to line 2. Cabral, Jr. et al. disclose embodiments in which the metal layer reacts with at least the silicon layer (column 5, lines 22-28) and with the silicon layer and a portion of the silicon-germanium layer (column 9, lines 8-15). Since Cabral, Jr. et al. recognize the problem associated with forming the silicide directly on the silicon-germanium and provide a solution by forming a sacrificial silicon layer, it would have been obvious to one skilled in the art to use a sacrificial silicon layer in the known method of Xiang et al.

Although Xiang et al. disclose forming a silicon-germanium layer within the substrate in each of the source and drain regions, as shown in figures 3d and 3e, Xiang et al. do not disclose that the silicon-germanium layer is configured to exert a compressive stress in the channel region of the substrate. However, the presence of silicon-germanium at each side of the channel region in the known method of Xiang et al. *inherently* results in the exertion of a compressive stress on the channel region. This

stress increases the mobility of carriers in the channel region and, thus, increases the current flowing through the transistor and its switching speed.

***Conclusion***

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to M. Wilczewski whose telephone number is (571) 272-1849. The examiner can normally be reached on Monday - Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on 571-272-2429. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.



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